查询MBR10H100CTG供应商

MBR10H100CT

SWITCHMODE™ Power Rectifier 100 V, 10 A

Features and Benefits

- Low Forward Voltage: 0.61 V @ 125°C
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 10 A Total (5.0 A Per Diode Leg)
- Guard−Ring for Stress Protection
- Pb−Free Package is Available

Applications

- Power Supply − Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube

MAXIMUM RATINGS

Please See the Table on the Following Page

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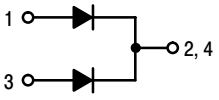
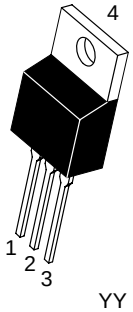
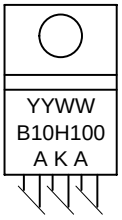
SCHOTTKY BARRIER RECTIFIER 10 AMPERES 100 VOLTS





TO−220AB CASE 221A PLASTIC

MARKING DIAGRAM



YY = Year
WW = Work Week
B10H100 = Device Code
AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBR10H100CT	TO−220	50 Units/Rail
MBR10H100CTG	TO−220 (Pb−Free)	50 Units/Rail

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MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R) T_C = 168°C	$I_{F(AV)}$	5.0	A
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) T_C = 165°C	I_{FRM}	10	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	180	A
Operating Junction Temperature (Note 1)	T_J	+175	°C
Storage Temperature	T_{stg}	− 65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs
Controlled Avalanche Energy (see test conditions in Figures 10 and 11)	W_{AVAL}	100	mJ
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

THERMAL CHARACTERISTICS

Maximum Thermal Resistance − Junction−to−Case − Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Maximum Instantaneous Forward Voltage (Note 2) (I_F = 5.0 A, T_C = 25°C) (I_F = 5.0 A, T_C = 125°C) (I_F = 10 A, T_C = 25°C) (I_F = 10 A, T_C = 125°C)	v_F	 0.73 0.61 0.85 0.71	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T_C = 125°C) (Rated DC Voltage, T_C = 25°C)	i_R	 4.5 0.0035	mA

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.
2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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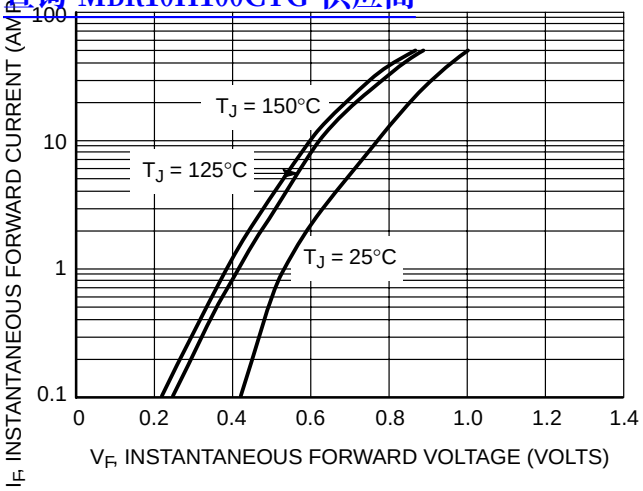

Figure 1. Typical Forward Voltage

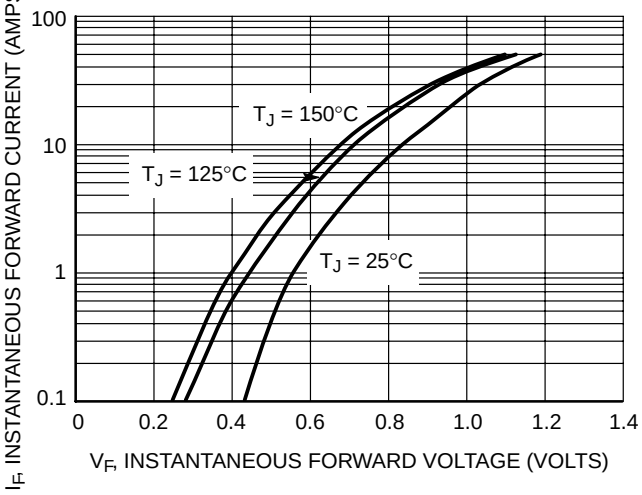

Figure 2. Maximum Forward Voltage

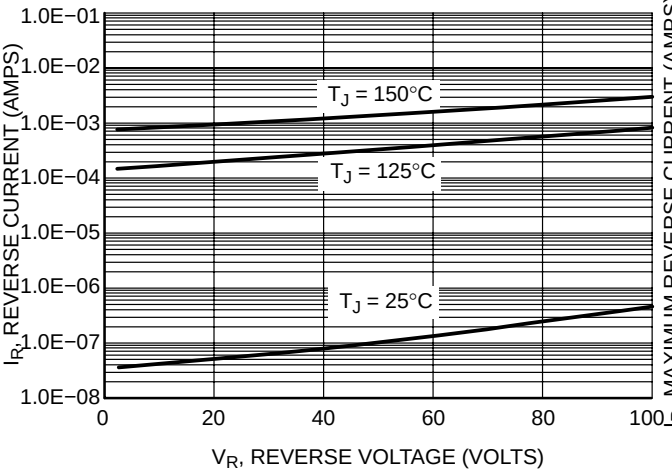

Figure 3. Typical Reverse Current

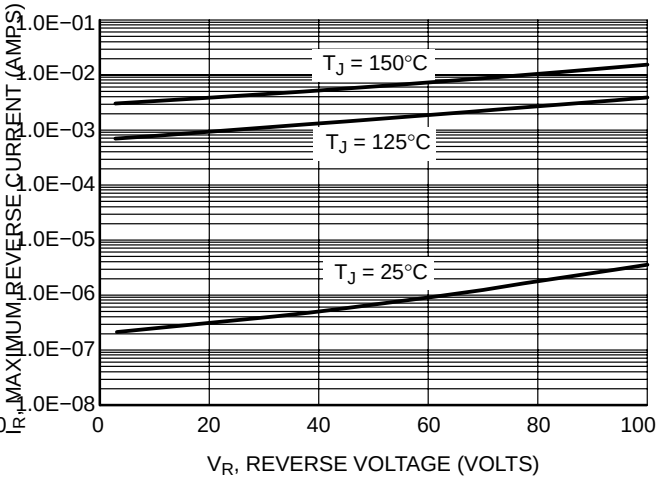

Figure 4. Maximum Reverse Current

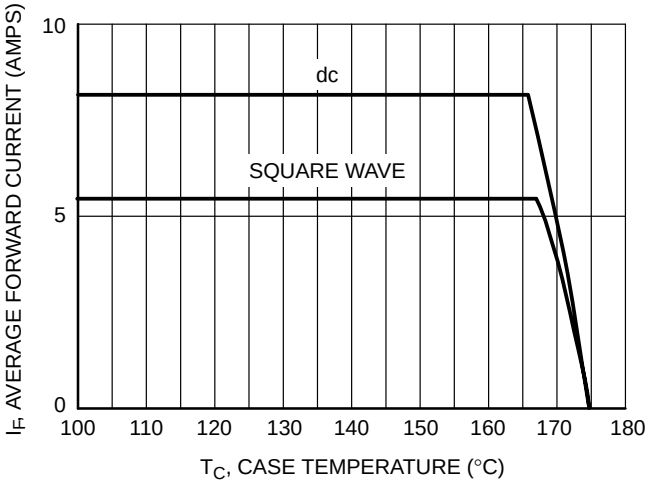

Figure 5. Current Derating

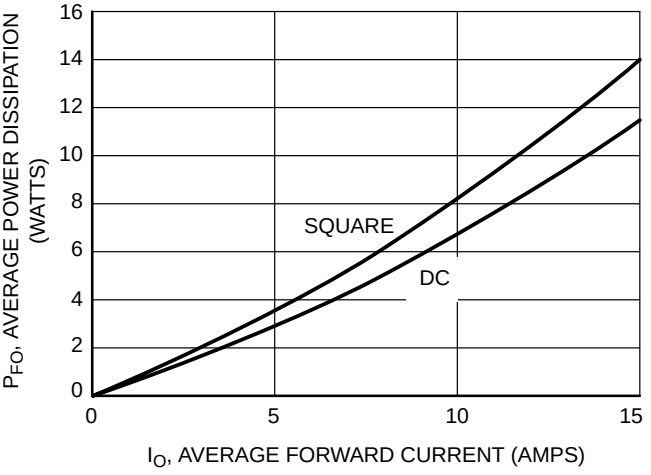

Figure 6. Forward Power Dissipation

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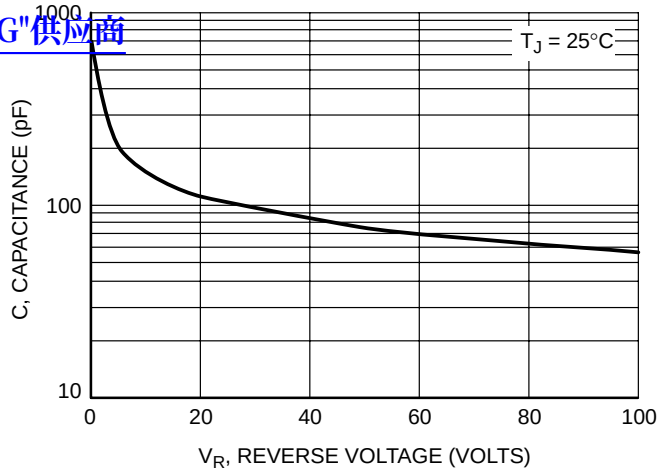

Figure 7. Capacitance

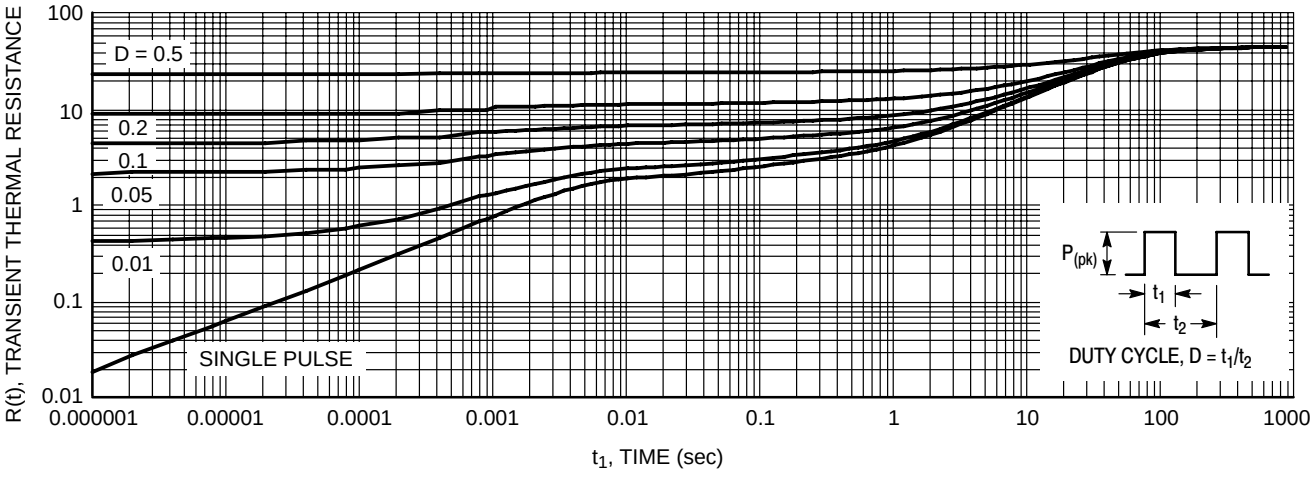

Figure 8. Thermal Response Junction−to−Ambient

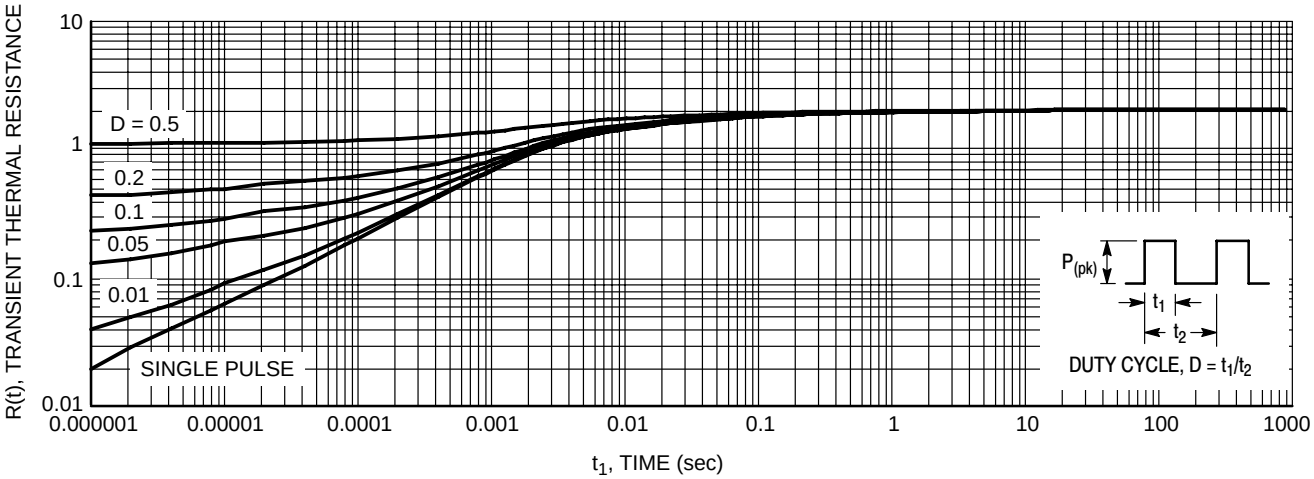

Figure 9. Thermal Response Junction−to−Case

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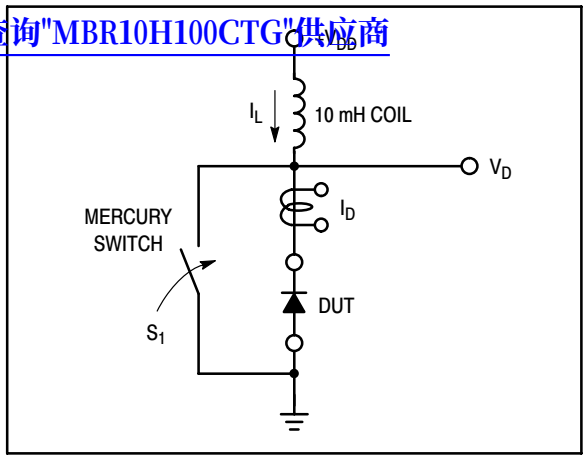

Figure 10. Test Circuit

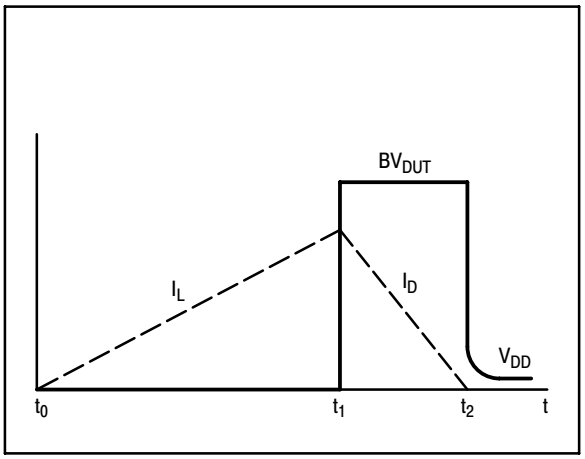

Figure 11. Current−Voltage Waveforms

The unclamped inductive switching circuit shown in Figure 10 was used to demonstrate the controlled avalanche capability of this device. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2.

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

EQUATION (1):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2 \left(\frac{BV_{DUT}}{BV_{DUT} - V_{DD}} \right)$$

EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2$$

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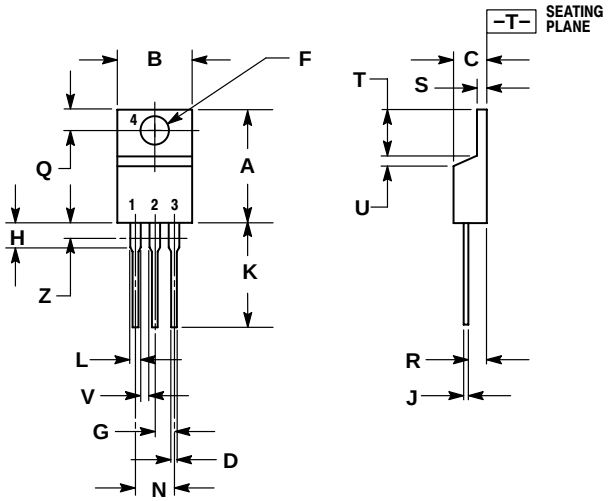
PACKAGE DIMENSIONS

TO−220
PLASTIC
CASE 221A−09
ISSUE AA



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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